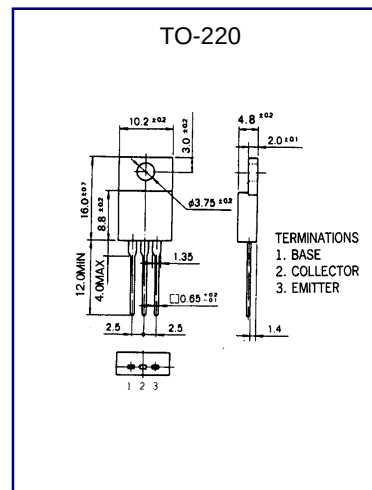




BUT11/11A

NPN SILICON TRANSISTOR

**HIGH VOLTAGE POWER
SWITCHING APPLICATIONS**



ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Emitter Voltage: BUT11	VCES	850	V
: BUT11A		1000	V
Collector-Emitter Voltage: BUT11	VCEO	400	V
: BUT11A		450	V
Emitter-Base Voltage	VEBO	9	V
Collector Current (DC)	IC	5	A
Collector Current (Pulse)	IC	10	A
Base Current (DC)	IB	2	A
Base Current (Pulse)	IB	4	A
Collector Dissipation (Tc=25°C)	PC	100	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-65~150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Emitter Sustaining Voltage : BUT11	VCE(SUS)	IC=100mA, IB=0	400			V
: BUT11A			450			V
Collector Cutoff Current : BUT11	ICES	VCE= 850V, VEB= 0			1	mA
: BUT11A					1	mA
Emitter Cutoff Current	IEBO	VCE= 1000V, VEB= 0			10	μA
Collector Emitter Saturation Voltage : BUT11	VCE(sat)	VEB= 9V, IC=0			1.5	V
: BUT11A		IC=3A, IB=0.6A			1.5	V
Base- Emitter Saturation Voltage : BUT11	VBE(sat)	IC=2.5A, IB=0.5A			1.3	V
: BUT11A					1.3	V
Turn-On Time	ton	IC=3A, IB=0.6A			1	μS
Storage Time	tstg	IC=2.5A, IB=0.5A			4	μS
Fall Time	tf	VCC= 250V, IC=2.5A, IB1= IB2=0.5A			0.8	μS